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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

Didier DUTARTRE and Patrick JERIER

Serial No: Filed:

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For:

METHOD OF EPITAXY ON A SILICON SUBSTRATE COMPRISING

AREAS HEAVILY DOPED WITH ARSENIC

Examiner:

Unassigned

Art Unit:

1762

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

The undersigned hereby certifies that this document is being placed in the United States mail with first-class postage attached, addressed to Box Missing Parts, Commissioner for Patents, Washington, D.C. 20231 on December 18, 2001.

Eileen Casey

Box Missing Parts Commissioner For Patents Washington, D.C. 20231

Sir:

PRELIMINARY AMENDMENT

Prior to examination, please amend this application as follows:

IN THE CLAIMS

Please cancel claims 1-9 without prejudice or disclaimer.

Please add the following new claims.

- 10. A method of vapor phase epitaxial deposition of silicon on a silicon substrate including areas containing dopants at high concentration, while avoiding an autodoping of the epitaxial layer by the dopants, including the steps of:
 - a) performing a first epitaxial deposition;
 - b) performing an anneal after step a);